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WHAT IS CLAIMED IS:

 A semiconductor substrate stock/transfer vessel, which is an openable/closeable sealed vessel used in a semiconductor device manufacturing process and adapted to store or transfer a semiconductor substrate,

wherein said vessel incorporates at least one adsorbent capable of adsorbing an organic substance, and said adsorbent is mounted detachably.

- 2. A vessel according to claim 1, wherein said 10 vessel incorporates a semiconductor substrate carrier having a plurality of slots each capable of holding one semiconductor substrate, so that a plurality of semiconductor substrates are stored while being held by said semiconductor substrate carrier.
- 3. A vessel according to claim 1, wherein said adsorbent is a silicon wafer with a surface coated with an adsorbing agent.
 - 4. A vessel according to claim 3, wherein said adsorbing agent is active carbon or an ion-exchange resin.
- 5. A vessel according to claim 1, wherein said adsorbent is a silicon wafer with a surface having a Si-F bond.
 - 6. A vessel according to claim 2, wherein said adsorbent is mounted in an empty slot of said semiconductor substrate carrier.

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- 7. A vessel according to claim 1, wherein said adsorbent is mounted in a space defined between an inner wall of said stock/transfer vessel and an outer wall of said semiconductor substrate carrier.
- 8. A vessel according to claim 1, wherein said adsorbent is made of active carbon or an ion-exchange resin.
 - 9. A vessel according to claim 1, wherein said adsorbent is made of active carbon or an ion-exchange resin.
 - A method of manufacturing a semiconductor device 10. wherein semiconductor substrate is stored in stock/transfer vessel incorporating at least one adsorbent capable of adsorbing an organic substance during an operation wait time between respective steps manufacturing said semiconductor device, said adsorbent being mounted detachably.
 - 11. A method according to claim 10, wherein the steps of manufacturing said semiconductor device include the step of forming a gate oxide film, the step of forming a polysilicon film, and the step of forming a contact hole.
 - 12. A method according to claim 10, wherein said vessel incorporates a semiconductor substrate carrier having a plurality of slots each capable of holding one semiconductor substrate, and a plurality of semiconductor

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substrates are stored while being held by said semiconductor substrate carrier.

- 13. A method according to claim 10, wherein said adsorbent is a silicon wafer with a surface coated with an adsorbing agent.
- 14. A method according to claim 13, wherein said adsorbing agent is active carbon or an ion-exchange resin.
- 15. A method according to claim 10, wherein said adsorbent is a silicon wafer with a surface having a Si-F bond.
- 16. A method according to claim 12, wherein said adsorbent is mounted in an empty slot of said semiconductor substrate carrier.
- 17. A method according to claim 10, wherein said
 15 adsorbent is mounted in a space defined between an inner
 wall of said stock/transfer vessel and an outer wall of
 said semiconductor substrate carrier.
- 18. A method according to claim 10, wherein said adsorbent is made of active carbon or an ion-exchange 20 resin.